

**isc Silicon NPN Power Transistor**

**BU508AF**

**DESCRIPTION**

- Collector-Emitter Sustaining Voltage-  
:  $V_{CEO(SUS)} = 700V$  (Min)
- High Switching Speed

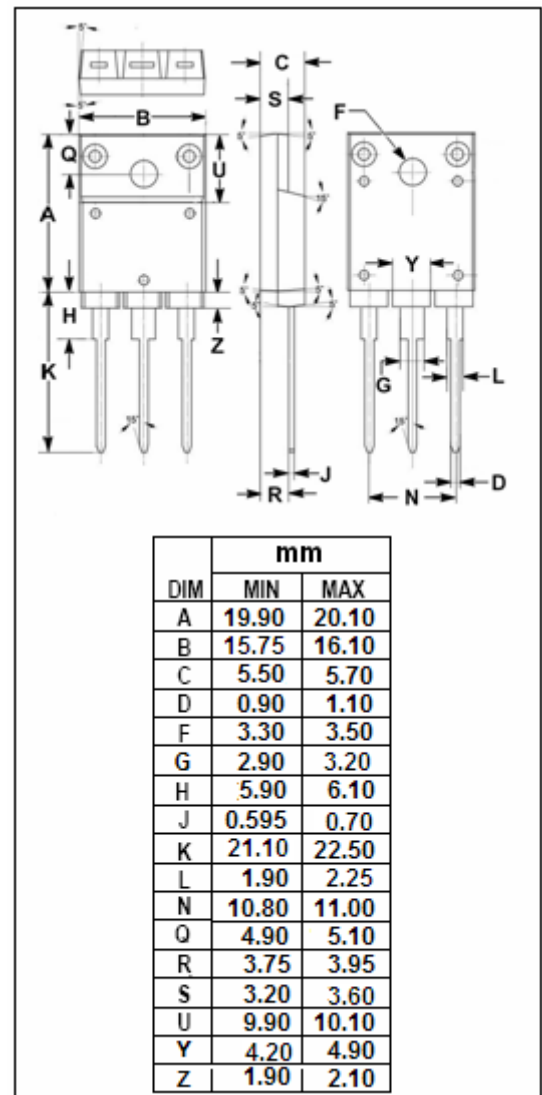
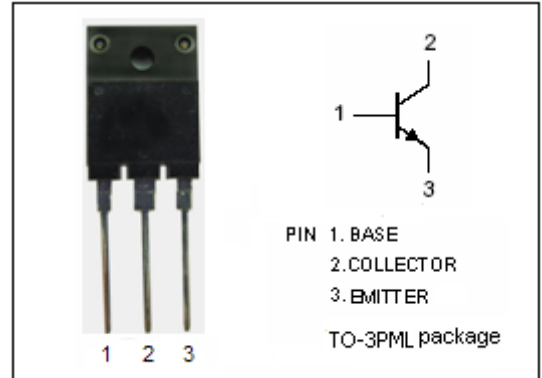
**APPLICATIONS**

- Designed for use in horizontal deflection circuits of color TV receivers.

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^{\circ}C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	1500	V
$V_{CEO}$	Collector-Emitter Voltage	700	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current- Continuous	8	A
$I_{CM}$	Collector Current-Peak	15	A
$I_B$	Base Current- Continuous	4	A
$I_{BM}$	Base Current-Peak	6	A
$P_C$	Collector Power Dissipation @ $T_C=25^{\circ}C$	60	W
$T_J$	Junction Temperature	150	$^{\circ}C$
$T_{stg}$	Storage Temperature Range	-65~150	$^{\circ}C$

SYMBOL	PARAMETER	MAX	UNIT
$R_{thj-c}$	Thermal Resistance, Junction to Case	2.5	$^{\circ}C/W$



**isc Silicon NPN Power Transistor****BU508AF****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=10\text{mA}; I_B=0$	700			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=4.5\text{A}; I_B=2.0\text{A}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=4.5\text{A}; I_B=2.0\text{A}$			1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=1500\text{V}; I_E=0$			1.0	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=5.0\text{V}; I_C=0$			10	mA
$h_{FE-1}$	DC Current Gain	$I_C=0.1\text{A}; V_{CE}=5\text{V}$	6		30	
$h_{FE-2}$	DC Current Gain	$I_C=4.5\text{A}; V_{CE}=5\text{V}$	2.25			
$C_{OB}$	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f_{test}=0.1\text{MHz}$		125		pF
$f_T$	Current-Gain—Bandwidth Product	$I_C=0.1\text{A}; V_{CE}=5\text{V}; f_{test}=1.0\text{MHz}$		7		MHz